# N-Channel 30-V (D-S) MOSFET

## **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- Fast switching speed

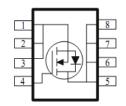
### **Typical Applications:**

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	5.8 @ V <sub>GS</sub> = 4.5V	24		
30	7.3 @ V <sub>GS</sub> = 2.5V	21		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Limit	Units			
Drain-Source Voltage			30	V			
Gate-Source Voltage		V <sub>GS</sub>	±12	v			
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	1	24				
	T <sub>A</sub> =70°C	I <sub>D</sub>	19	А			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	100				
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>s</sub>	6.1	А			
Dower Discipution <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	5	w			
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	U 'D	3.2	vv			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	R <sub>eja</sub>	25	°C/W		
	Steady State	ιν <sub>θ</sub> ja	65	C/vv		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

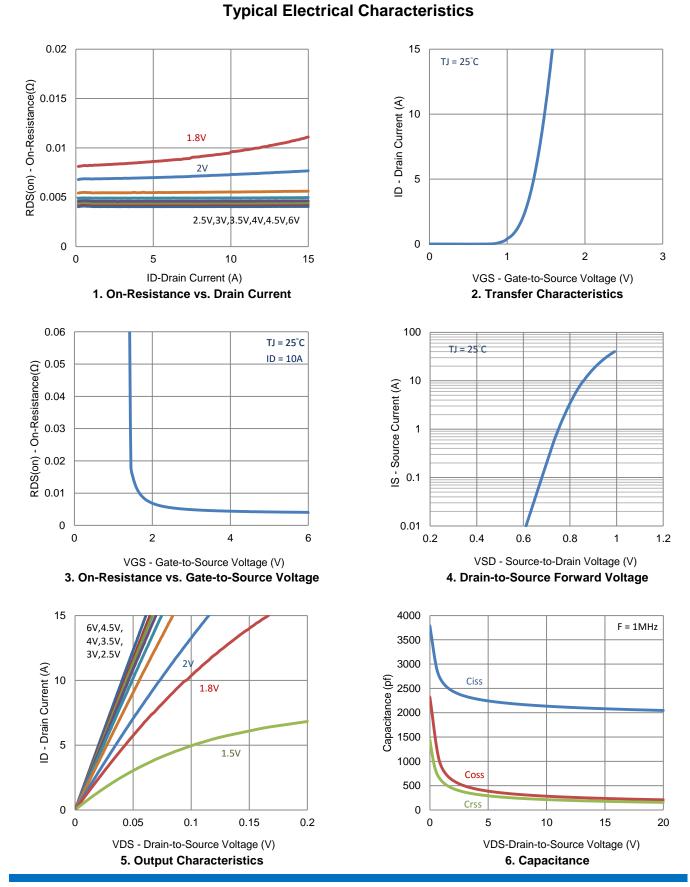
# **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V},  V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	$V_{DS} = 24 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$		1	uA	
	IDSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	35			А	
Drain Course On Desistance a	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 12 \text{ A}$			5.8	m0	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$			7.3	mΩ	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 12 \text{ A}$		61		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = 3.0 \text{ A}, V_{GS} = 0 \text{ V}$		0.79		V	
		Dynamic <sup>b</sup>					
Total Gate Charge	Qg	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V},$		30		nC	
Gate-Source Charge	Q <sub>gs</sub>	$v_{DS} = 30 \text{ V}, v_{GS} = 4.3 \text{ V},$ $I_{D} = 10 \text{ A}$		2.6			
Gate-Drain Charge	$Q_gd$	$I_D = 10$ A		8.4			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = 30 \text{ V}, \text{ R}_{L} = 3 \Omega,$		16			
Rise Time	t <sub>r</sub>	$v_{DS} = 30 \text{ v}, \text{ K}_{L} = 3 \Omega,$ $I_{D} = 10 \text{ A},$		42		ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		148			
Fall Time	t <sub>f</sub>	$v_{\text{GEN}} = 10 v$ , $v_{\text{GEN}} = 0.22$		52			
Input Capacitance	C <sub>iss</sub>			2082			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		237		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			178			

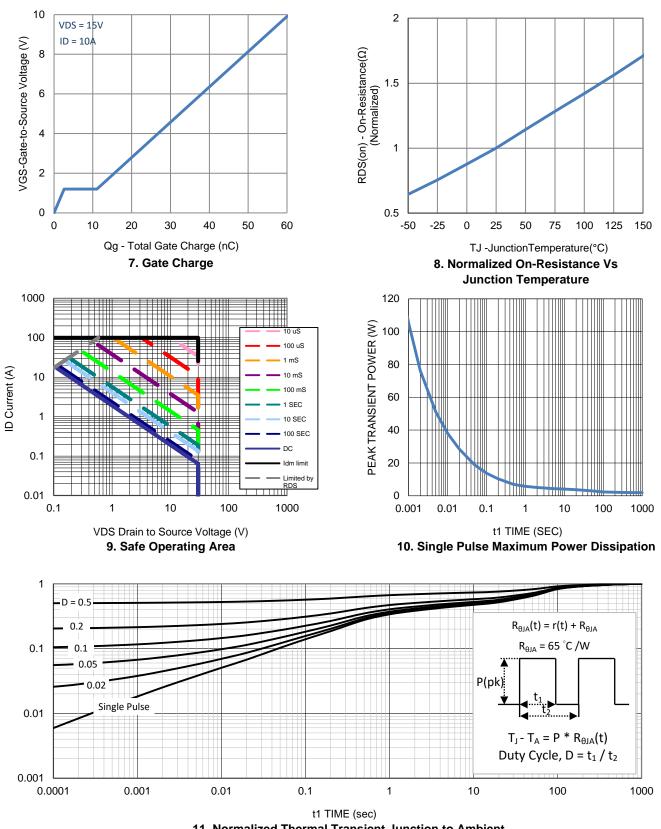
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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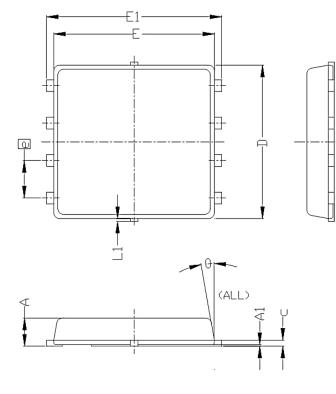
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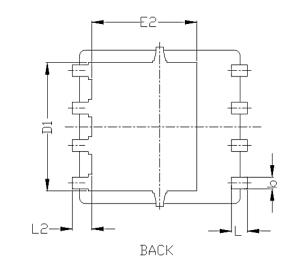


## **Typical Electrical Characteristics**

**11. Normalized Thermal Transient Junction to Ambient** 

# Package Information





SYMBOLS DIMENS		IONS IN MILLIMETERS		DIMENSIONS IN INCHES			
STNDOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0.15	0.20	0.25	0.006	0.008	0.010	
D	5.20 BSC			0.205 BSC			
D1	4.35 BSC			0.171 BSC			
E	5.55 BSC			0.219 BSC			
E1	6.05 BSC			0.238 BSC			
E2	3.62 BSC			0.143 BSC			
e	1.27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	